

## Product Summary

Device	BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
Q2	30V	21mΩ @ V <sub>GS</sub> = 10V	8.5A
		32mΩ @ V <sub>GS</sub> = 4.5V	7.2A
Q1	-30V	39mΩ @ V <sub>GS</sub> = -10V	-7A
		53mΩ @ V <sub>GS</sub> = -4.5V	-5.6A

## Description

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

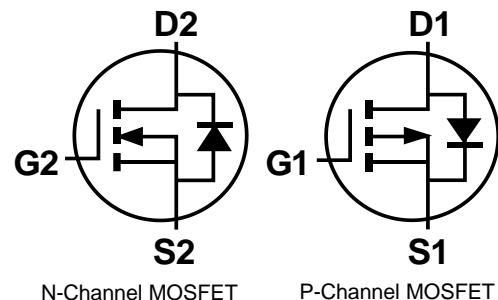
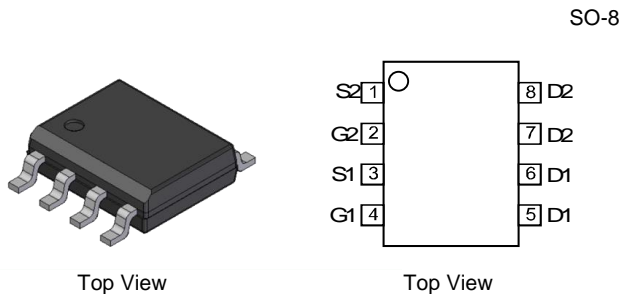
- Power Management Functions
- Analog Switch
- Load Switch

## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.** <https://www.diodes.com/quality/product-definitions/>
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMC3021LSDQ](#))**

## Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (Approximate)

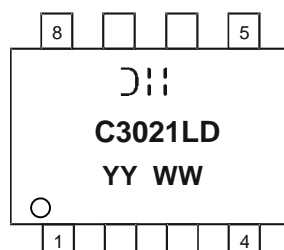


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMC3021LSD-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



DII = Manufacturer's Marking  
 C3021LD = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 20 = 2020)  
 WW = Week (01 to 53)

**Maximum Ratings N-CHANNEL – Q2** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	8.5	A
		T <sub>A</sub> = +85°C		7.1	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	40	A

**Maximum Ratings P-CHANNEL – Q1** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-7.0	A
		T <sub>A</sub> = +85°C		-4.5	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-30	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	50	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics N-CHANNEL – Q2** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.45	2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	14	21	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7A
		—	18	32		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.6A
Forward Transfer Admittance	Y <sub>fs</sub>	—	8.1	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 7A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	0.7	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	767	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	110	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	105	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.4	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	7.8	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 9A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	16.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	1.8	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	2.5	—	nC	
Turn-On Delay Time	t <sub>d(ON)</sub>	—	5.0	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>r</sub>	—	4.5	—	ns	
Turn-Off Delay Time	t <sub>d(OFF)</sub>	—	26.3	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	8.55	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

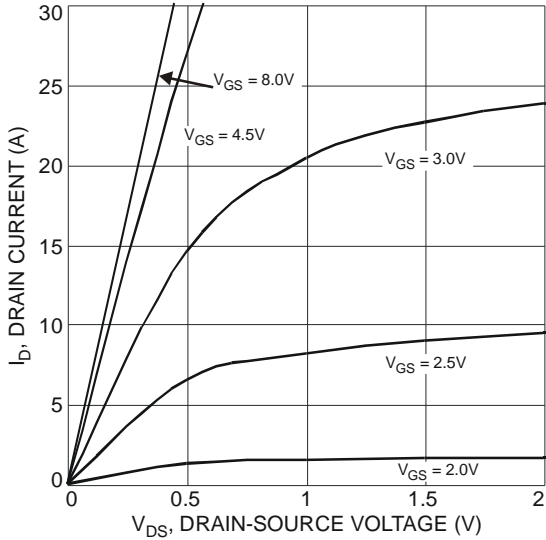


Fig. 1 Typical Output Characteristics

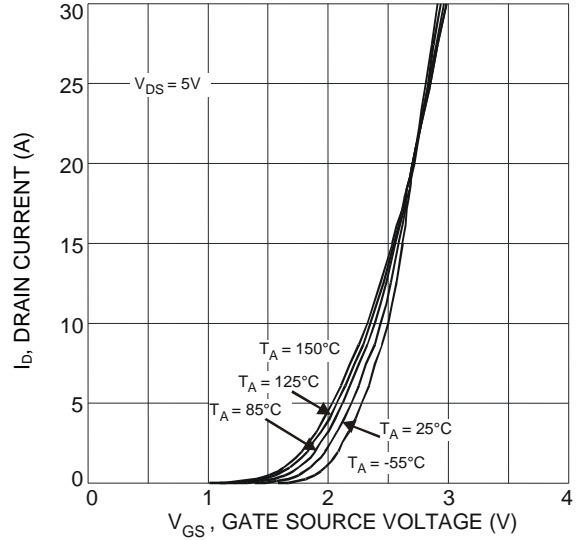


Fig. 2 Typical Transfer Characteristics

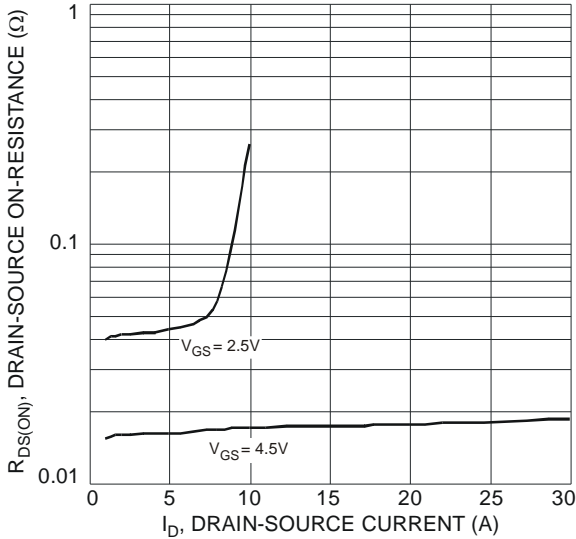


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

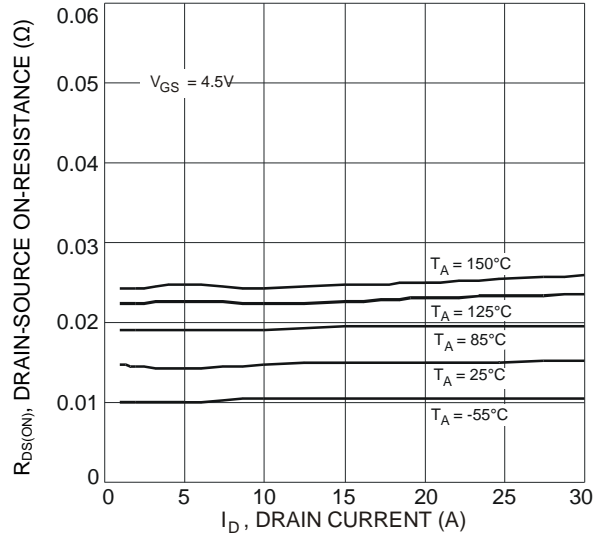


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

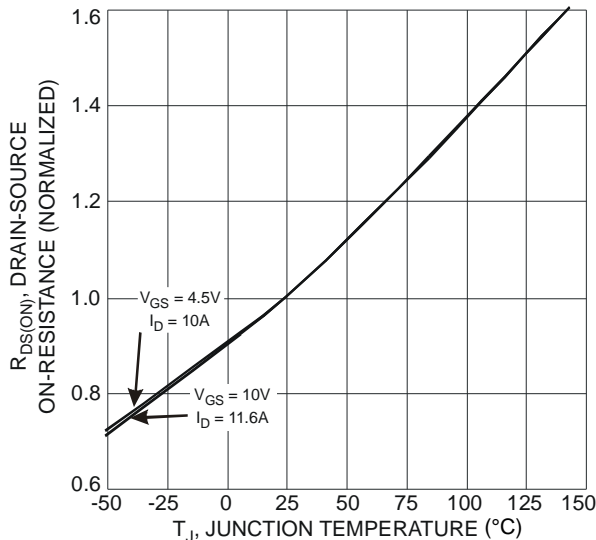


Fig. 5 On-Resistance Variation with Temperature

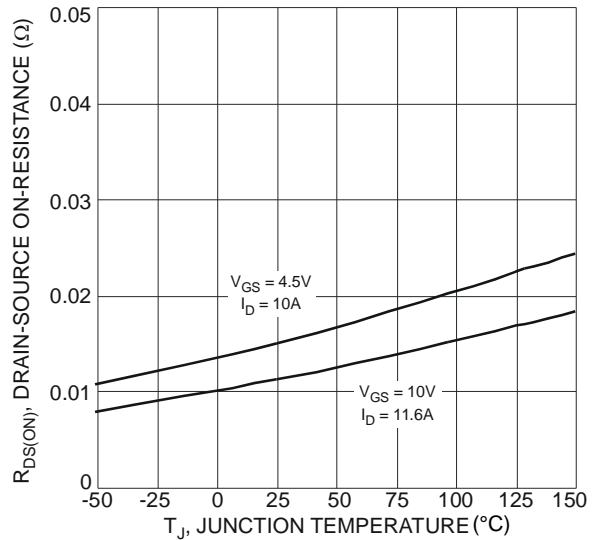


Fig. 6 On-Resistance Variation with Temperature

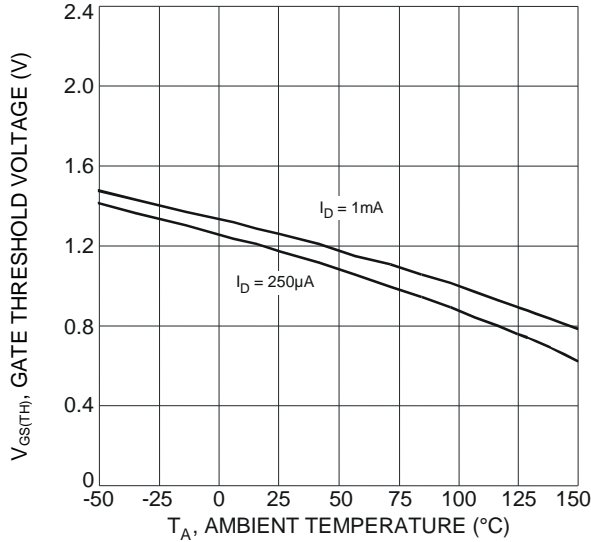


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

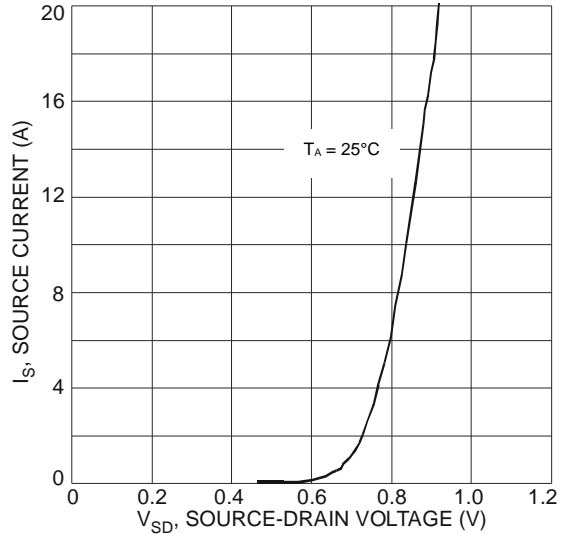


Fig. 8 Diode Forward Voltage vs. Current

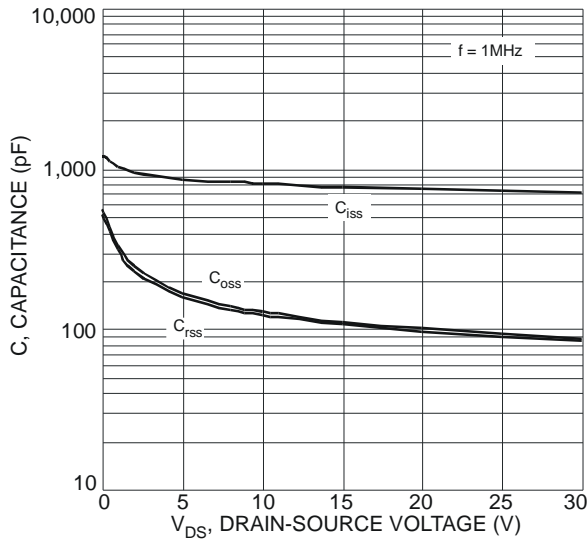


Fig. 9 Typical Capacitance

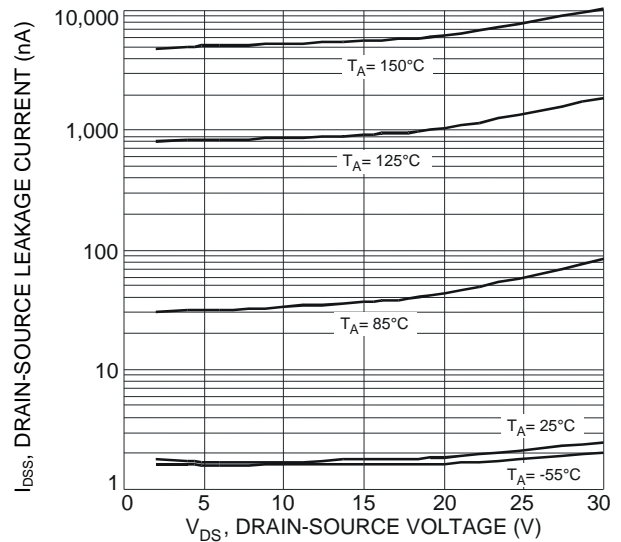


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

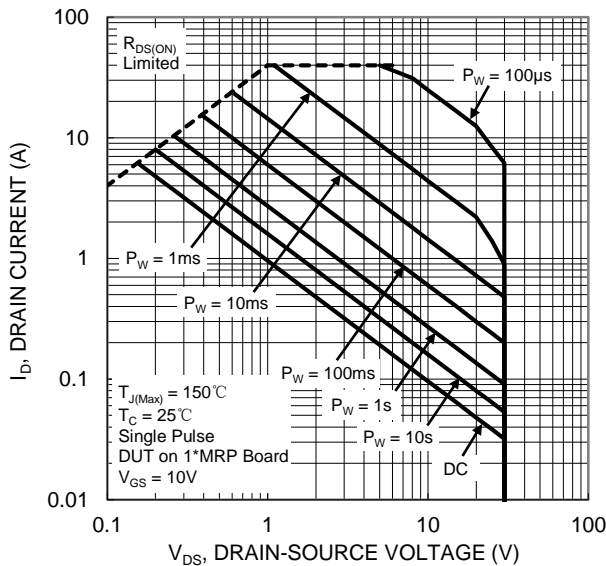


Fig. 11 SOA, Safe Operation Area

**Electrical Characteristics P-CHANNEL – Q1** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	-1.7	-2.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	30	39	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.3A
			42	53		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.7A
Forward Transfer Admittance	Y <sub>fs</sub>	—	7	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4.3A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	-0.75	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.7A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	1002	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	125	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	118	—	pF	
Gate Resistance	R <sub>g</sub>	—	13	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	10.1	—	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -6A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	21.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	2.8	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	3.2	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	10.1	—	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>r</sub>	—	6.5	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	50.1	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	22.2	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to production testing.

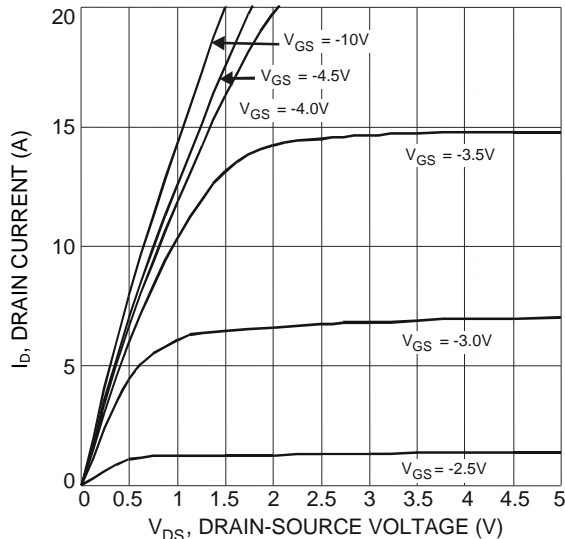


Fig. 12 Typical Output Characteristics

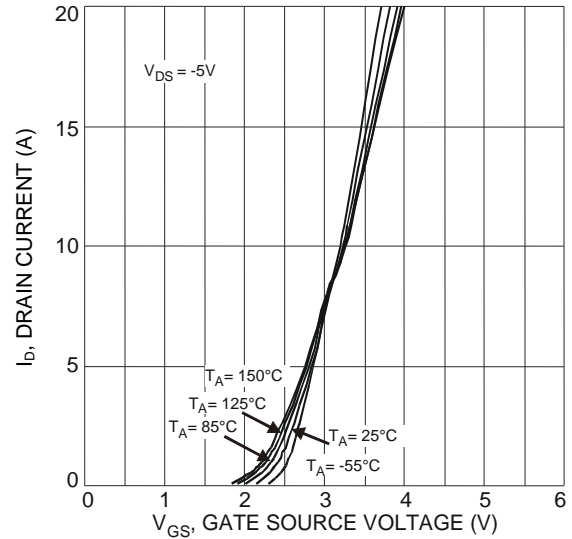


Fig. 13 Typical Transfer Characteristics

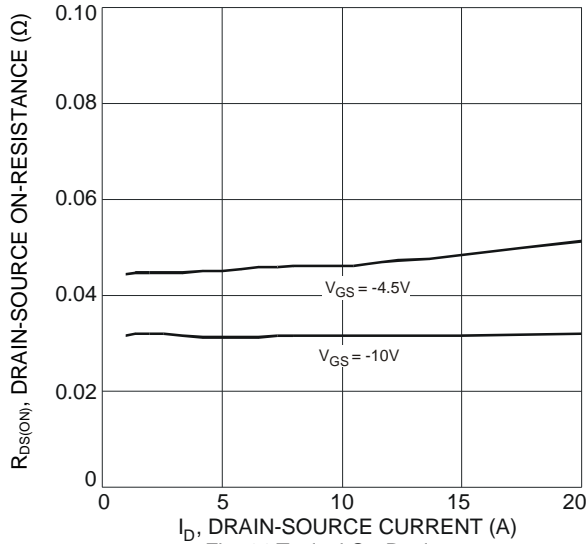


Fig. 14 Typical On-Resistance vs. Drain Current and Gate Voltage

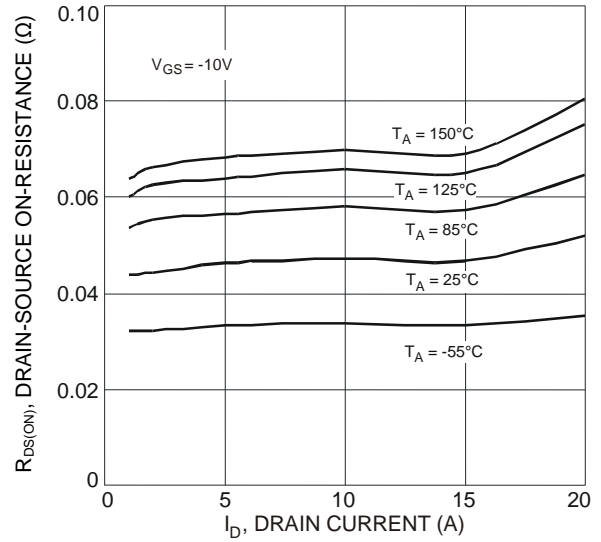


Fig. 15 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

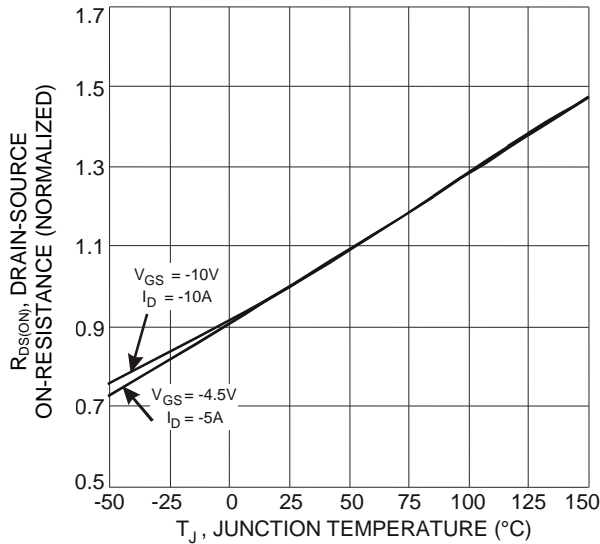


Fig. 16 On-Resistance Variation with Temperature

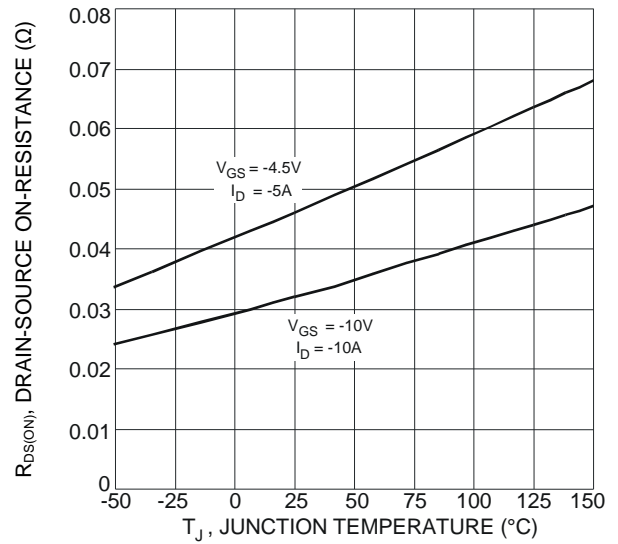


Fig. 17 On-Resistance Variation with Temperature

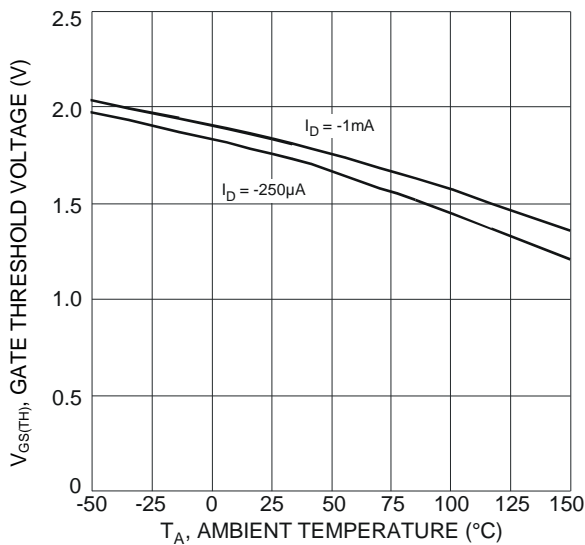


Fig. 18 Gate Threshold Variation vs. Ambient Temperature

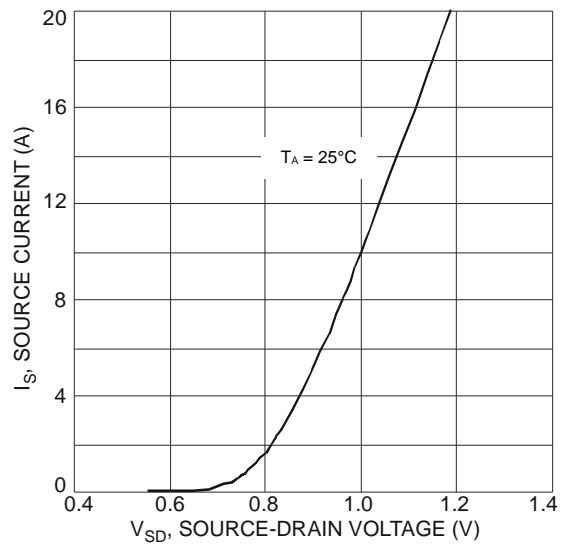
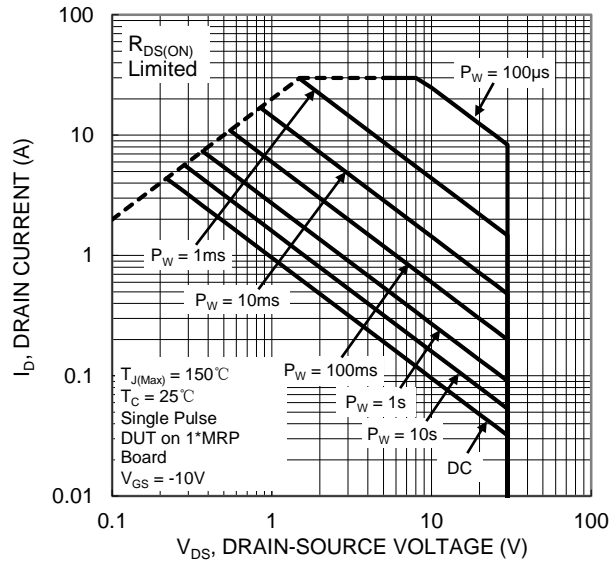
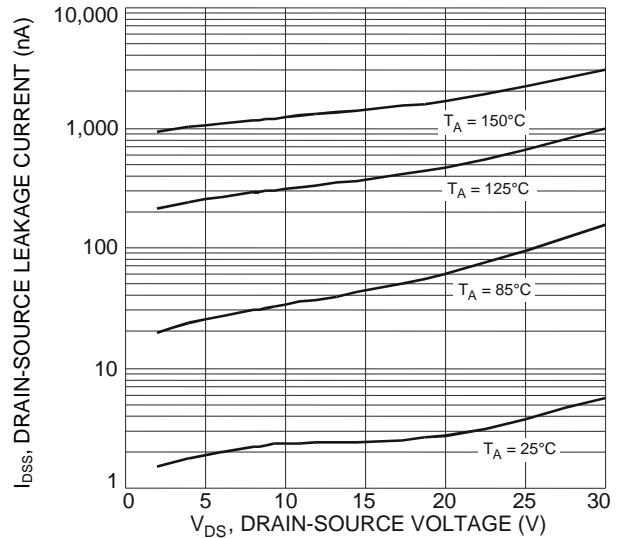
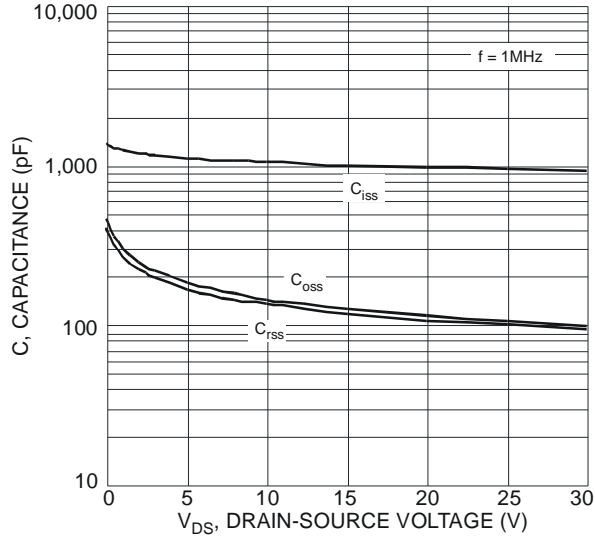


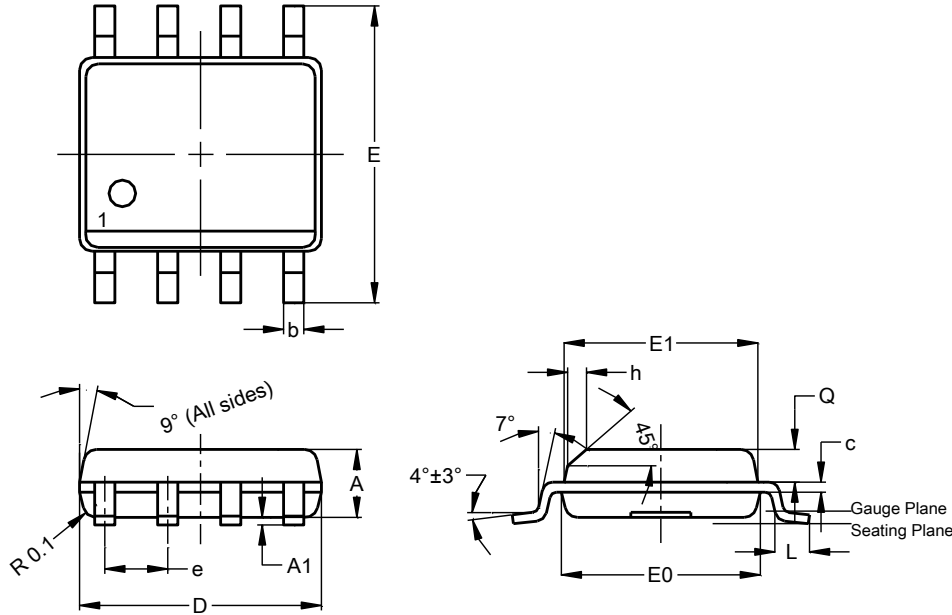
Fig. 19 Diode Forward Voltage vs. Current



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**

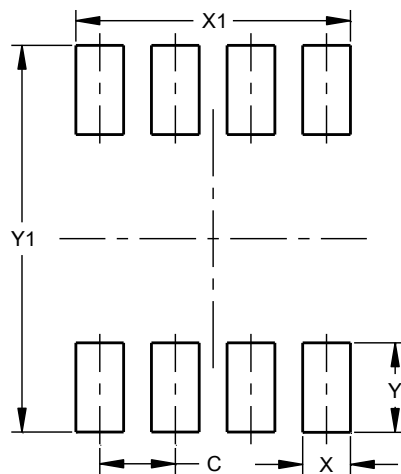


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	--	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50



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